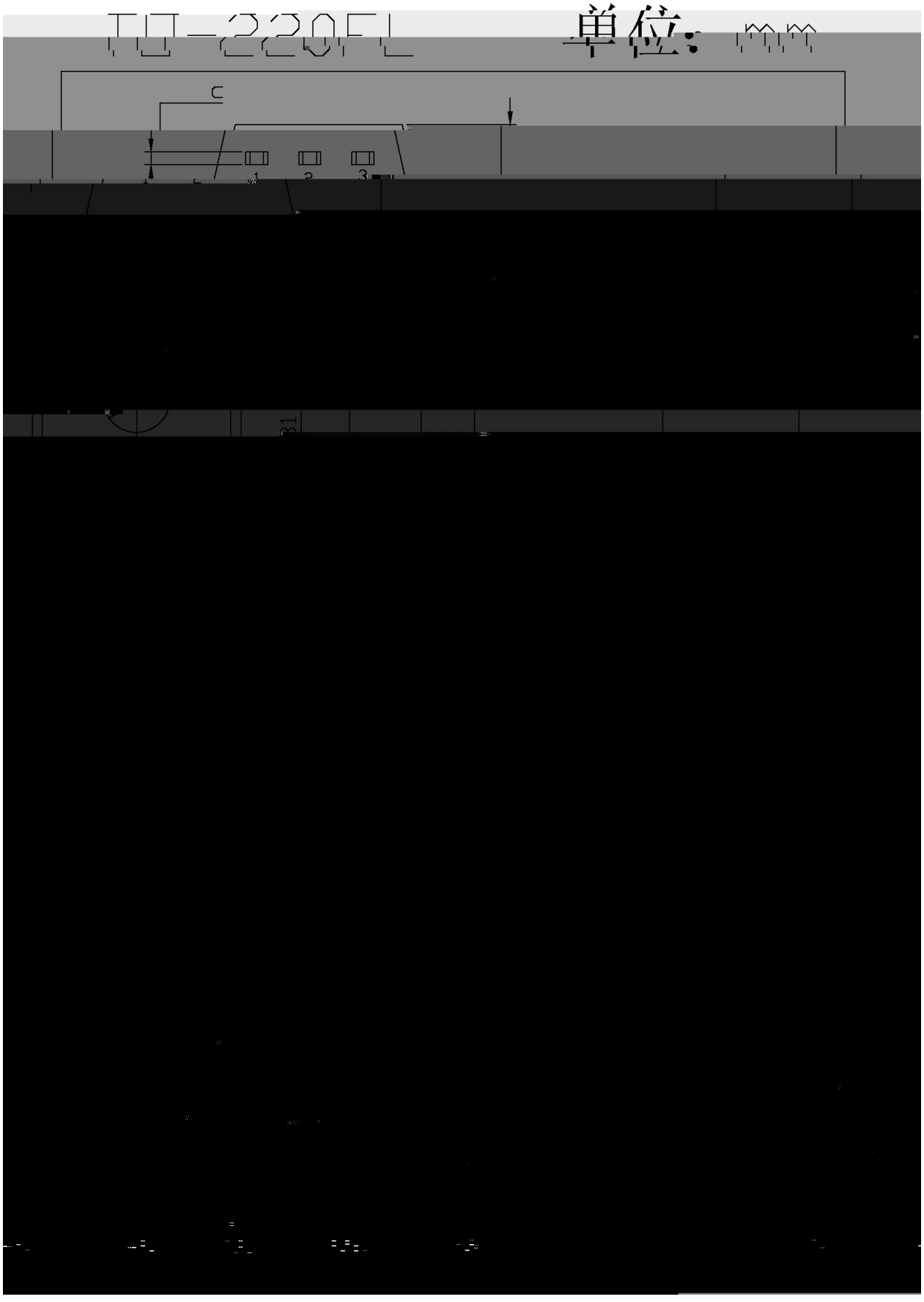
TO-220FL N MOS
N-CHANNEL MOSFET in a TO-220FL Plastic Package.

Low gate charge, low crss, fast switching,Have good Electromagnetic Interference porformance.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	10	A
Drain Current - Pulsed	I_{DM}	40	A
Gate-Source Voltage	V_{GSS}	±30	V
Sin ed Avalanche Energy	E_{AS}	280	mJ
rrent	I_{AR}	8	A
wer Diss on	P_D(Tc=25)	40	W
perating ar torage Temp ature Range	T_J,T_{STG}	-55 to 150	
hermal Res ce, Junctio Ambient	$R_{\theta JA}$	62.5	/W
hermal Resis ce, Junctio Case	$R_{\theta JC}$	3.1	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	650	680		V
Zero e Drain Current	I_{DSS}	V_{DS}=650V V_{GS}=0V			1.0	μA
Ga age Curr F ard	I_{GSS}	V_{GS}=±30V V_{DS}=0V			±10	μA
Thresho Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	2.0	3.2	4.0	V
ic Drain-S ce -Resistanc	$R_{DS(on)}$	V_{GS}=10V I_D=4.75A		0.73	0.85	Ω
ut Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		1550		pF
put Capacitance	C_{oss}			30		
erse Transfer Capacitanc	C_{rss}			9		
te Charge	Q_G	V_{DS}= 520V, I_D= 10.0A, V_{GS}= 10V		45		nC
Gate	Q_{GS}			6.8		
Gate-Drai	Q_{GD}			19		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=325V I_D=10A				
Single Pul va y	=25Ω V_{GS}= 10		T	T	21W	

ate-Dr


TO-220FL
单位：mm

